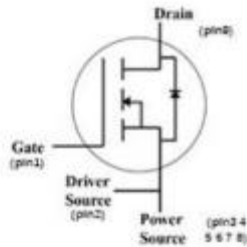
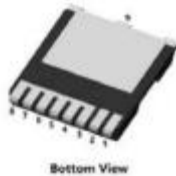


Silicon Carbide Power MOSFET (N-Channel Enhancement)

V_{DS}	750V
I_D (25°C)	61A
$R_{DS(on)}$	40mΩ



Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free, RoHS compliant

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- **Package:** TOLL
- **Terminals:** Tin plated leads
- **Polarity:** As marked

■Maximum Ratings ($T_c=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code			D207550TLYG3		
Drain source voltage @ $T_j=25^\circ\text{C}$	$V_{DS,max}$	V	750	$V_{GS}=0V$, $I_D=100\mu A$	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,max}$	V	-8/+22	Absolute maximum values (AC f > 1Hz, duty cycle < 1%)	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,op}$	V	-5/+18	Recommended operational values	
Continuous drain current @ $T_c=25^\circ\text{C}$	I_D	A	61	$V_{GS}=18V$, $T_c=25^\circ\text{C}$	Fig.17
Continuous drain current @ $T_c=100^\circ\text{C}$			41	$V_{GS}=18V$, $T_c=100^\circ\text{C}$	
Pulsed drain current	$I_{D(pulsed)}$	A	145	Pulse width t_p limited by $T_{j,max}$	Fig.22
Avalanche energy, Single Pulse	E_{AS}	mJ	627	$V_{DD}=75V$, $L=10mH$	
Power Dissipation	P_{TOT}	W	194.8	$T_c=25^\circ\text{C}$, $T_j = 175^\circ\text{C}$	Fig.16
Power Dissipation			97	$T_c=100^\circ\text{C}$, $T_j = 175^\circ\text{C}$	
Operating junction and Storage temperature range	T_j, T_{stg}	$^\circ\text{C}$	-55 to +175		
Soldering temperature	T_L	$^\circ\text{C}$	260	1.6mm (0.063") from case for 10s	
Mounting torque	T_M	Nm	0.6	M3 screw Maximum of mounting process: 3	



YJD207550TLYG3

■Static Electrical Characteristics (Tc=25℃ unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	$V_{GS(th)}$	V	2.0	3.0	4.0	$V_{DS}=V_{GS}, I_D=8mA$	Fig.4, 11
				2.2		$V_{DS}=V_{GS}, I_D=8mA, T_J=175^{\circ}C$	
Drain source breakdown voltage	$V_{(BR)DSS}$	V	750			$V_{GS}=0V, I_D=100\mu A$	
Drain source leakage current	I_{DSS}	μA		10	100	$V_{DS}=750V, V_{GS}=0V$	
Gate source leakage current	I_{GSS}	nA		10	100	$V_{GS}=18V, V_{DS}=0V$	
Current drain source on-state resistance	$R_{DS\ ON}$	m Ω		46		$V_{GS}=15V, I_D=20A$	Fig.5, 6, 7
				40	52	$V_{GS}=18V, I_D=20A$	
				60		$V_{GS}=15V, I_D=20A, T_J=175^{\circ}C$	
				55		$V_{GS}=18V, I_D=20A, T_J=175^{\circ}C$	
Transconductance	g_f	S		14.5		$V_{DS}=20V, I_D=20A$	Fig.4
				14		$V_{DS}=20V, I_D=20A, T_J=175^{\circ}C$	

■Dynamic Electrical Characteristics (Tc=25℃ unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	C_{iss}	pF		2542		$V_{DS}=500V, V_{GS}=0V, T_J=25^{\circ}C, f=1MHz, V_{AC}=25mV$	Fig.13, 14
Output capacitance	C_{oss}			132			
Reverse capacitance	C_{rss}			5			
Coss stored energy	E_{oss}	μJ		31			Fig.15
Gate source charge	Q_{gs}	nC		22		$V_{DS}=500V, V_{GS}=-5/+18V, I_D=20A$	Fig.12
Gate drain charge	Q_{gd}			38			
Gate charge	Q_g			82			
Internal gate resistance	R_g	Ω		1.5		$f=1MHz$	

■Switching Characteristics (Tc=25℃ unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on delay time	$t_{d(on)}$	ns		12.8		$V_{DD}=500V, V_{GS}=-5/+18V, I_D=20A, R_g=2.4\Omega, L=100\mu H$	Fig.21
Rise time	t_r			19			
Turn off delay time	$t_{d(off)}$	ns		23.2			
Fall time	t_f			8.3			



YJD207550TLYG3

Turn on switching energy	E_{on}	uJ		145.7		$V_{DD}=500V, V_{GS}=-5/+18V, I_D=20A,$ $R_g=2.4\Omega, L=100\mu H$	Fig.19, 20
Turn off switching energy	E_{off}			39.6			

■Body diode characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	V_{SD}	V		4.3		$V_{GS}=-5V, I_{SD}=10A$	Fig.8
				2.6		$V_{GS}=0V, I_{SD}=10A, T_J=175^\circ C$	Fig.9
Continuous diode forward current	I_S	A		32		$V_{GS}=-5V, T_C=25^\circ C$	
Reverse recovery time	t_{rr}	nS		16		$V_R=500V, V_{GS}=-5V, I_D=20A,$ $di/dt=1000A/\mu S$	
Reverse recovery charge	Q_{rr}	nC		149			
Peak reverse recovery current	I_{rrm}	A		7			

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Typ.
Thermal resistance	$R_{\theta J-C}$	$^\circ C/W$	0.77

■Typical Characteristics

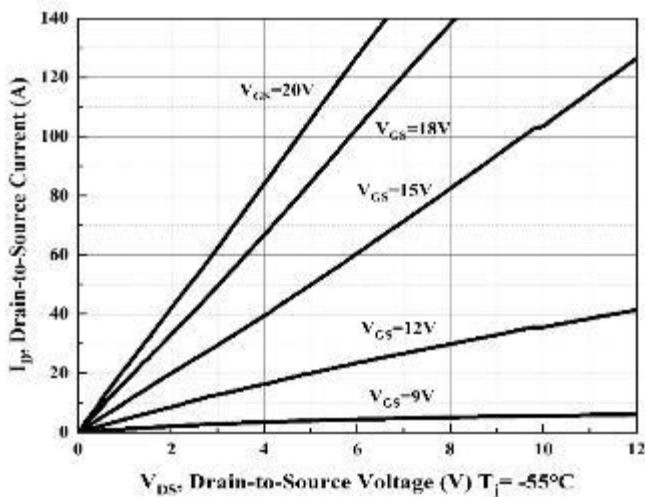


Figure 1. Output Characteristics T_j = -55°C

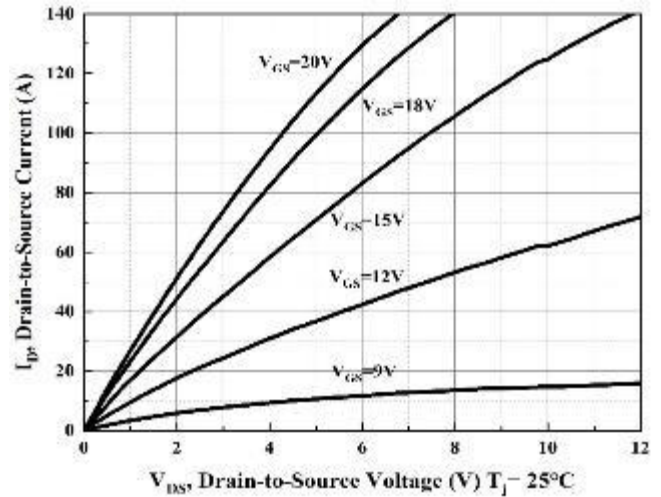


Figure2. Output Characteristics T_j = 25°C

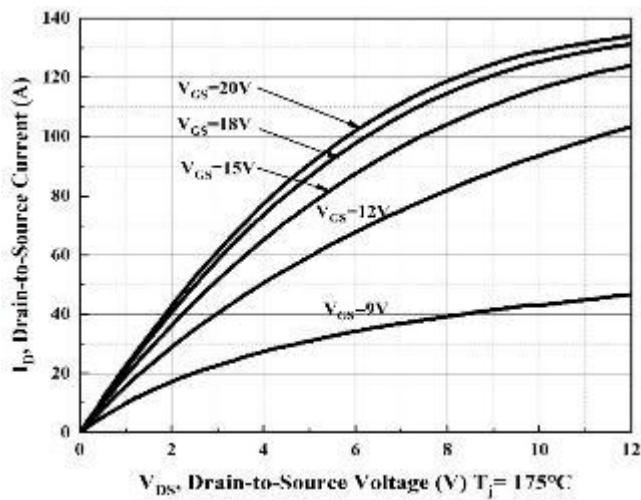


Figure 3. Output Characteristics $T_j = 175^\circ\text{C}$

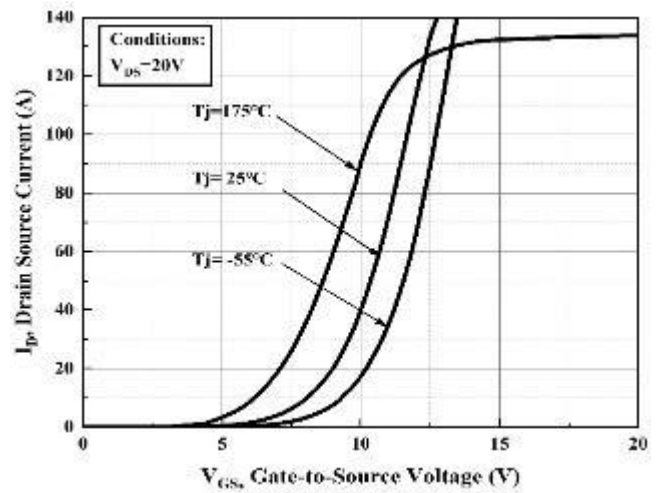


Figure 4. Transfer Characteristics for Various Junction Temperature

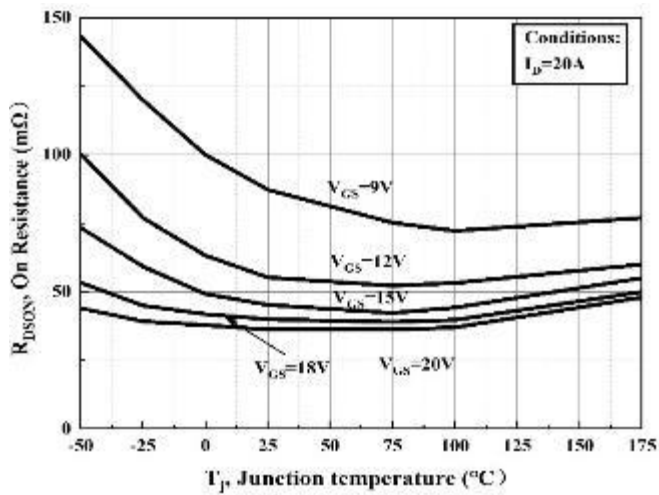


Figure 5. On-resistance vs. Temperature for Various Gate Voltage

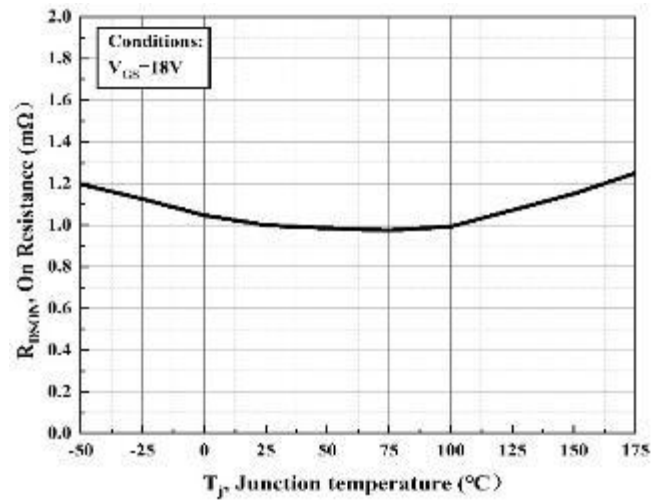


Figure 6. Normalized on-resistance vs. Temperature

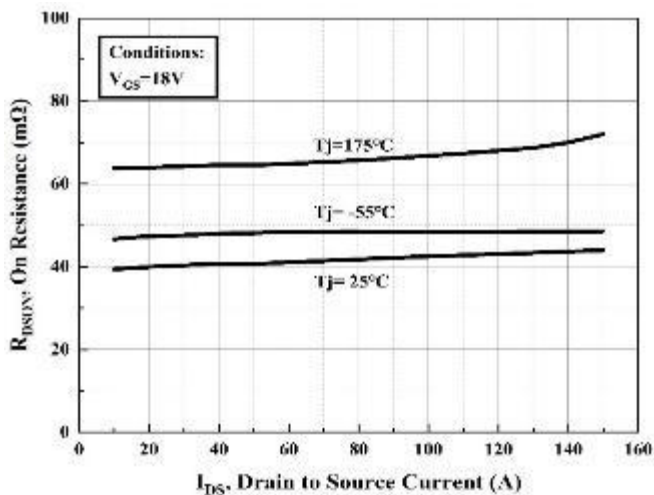


Figure 7. On-resistance vs. Drain Current

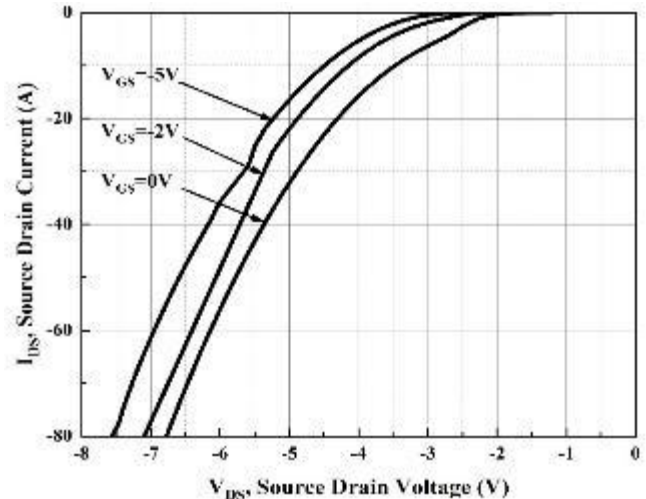


Figure 8. Body Diode Characteristic at $T_j = 25^\circ\text{C}$

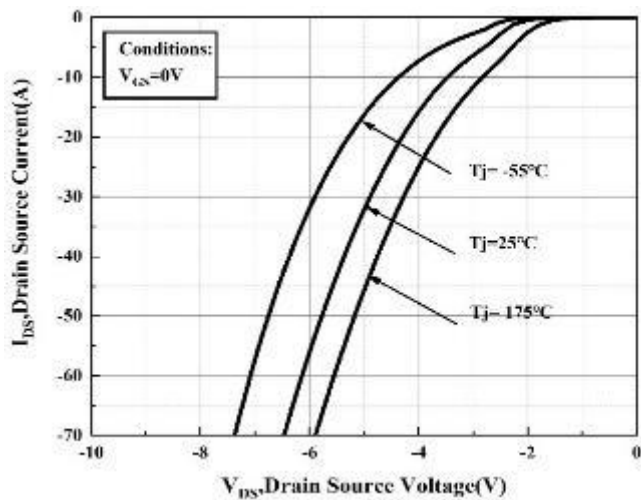


Figure 9. Body Diode Characteristic

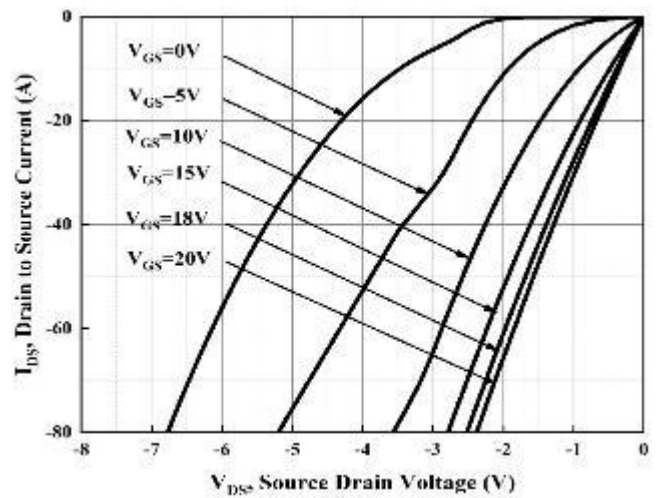


Figure 10. 3rd quadrant Characteristic at Tj= 25 °C

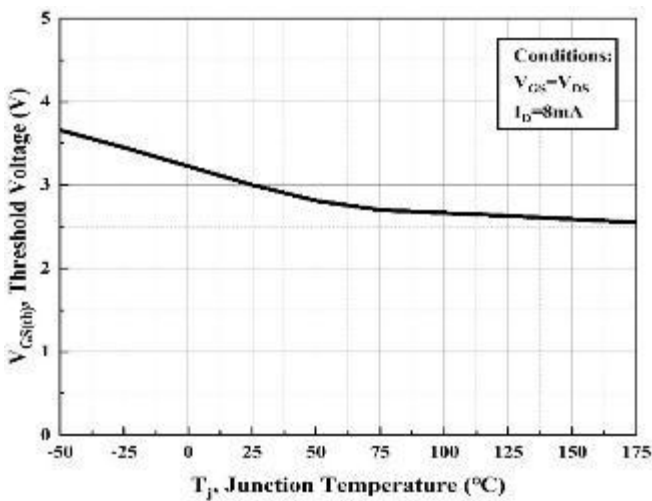


Figure 11. Threshold Voltage vs. Temperature

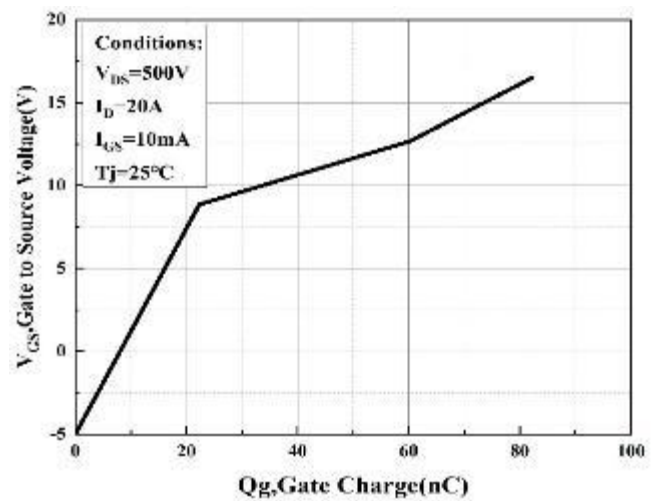


Figure 12. Gate Charge Characteristic

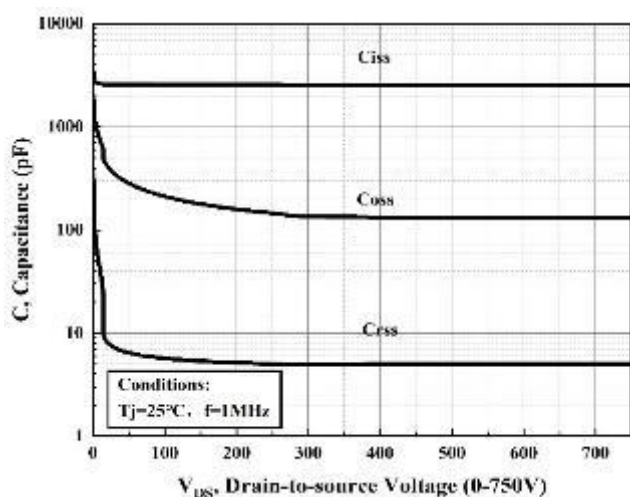


Figure 13. Capacitances vs. Drain Source Voltage (0-750V)

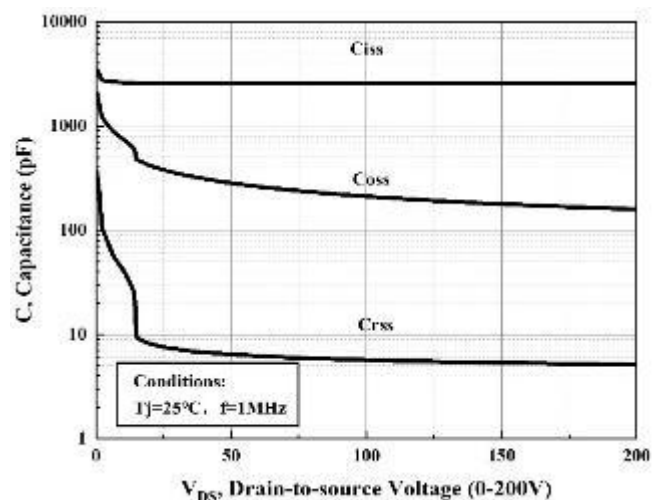


Figure 14. Capacitances vs. Drain Source Voltage (0-200V)

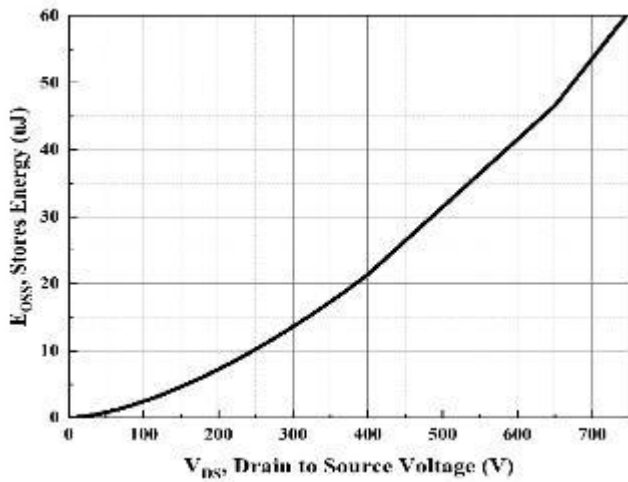


Figure 15. Output Capacitor Stored Energy

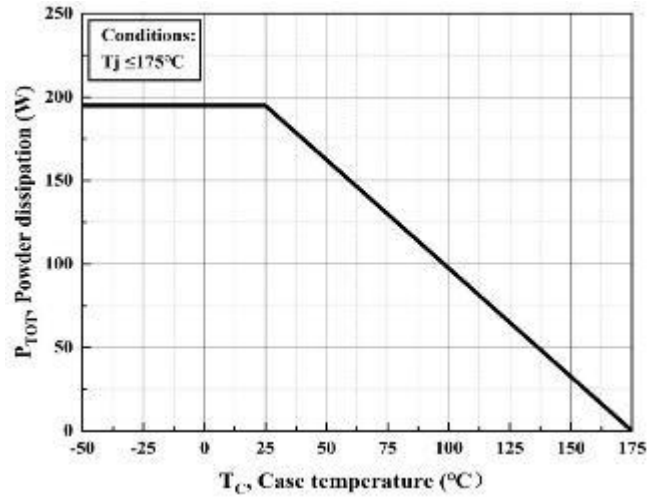


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

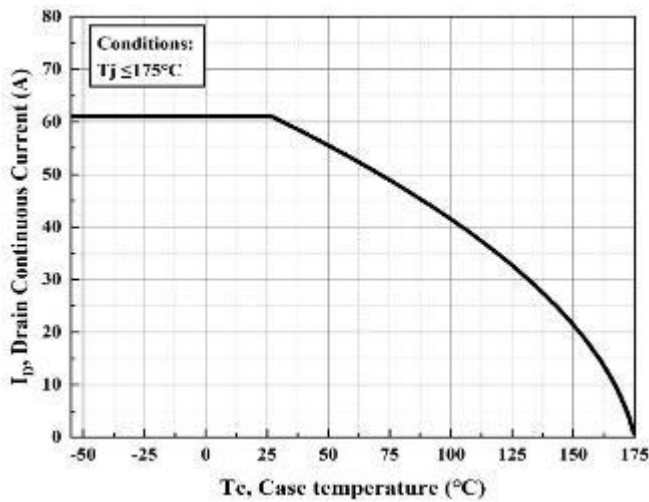


Figure 17. Continuous Drain Current Derating vs. Case Temperature

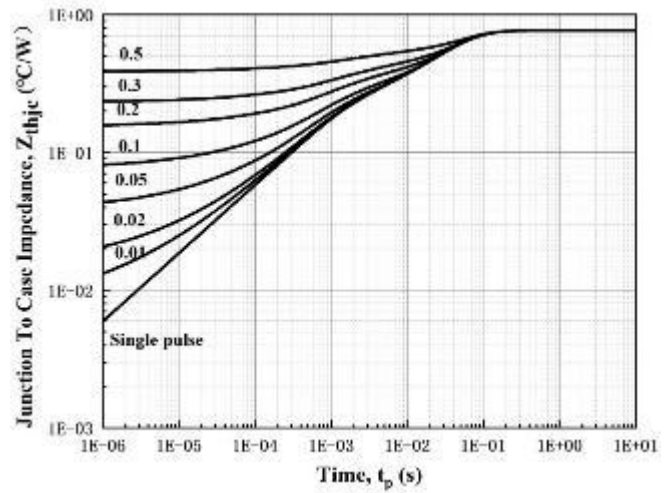


Figure18 Transient Thermal Impedance (Junction - Case)

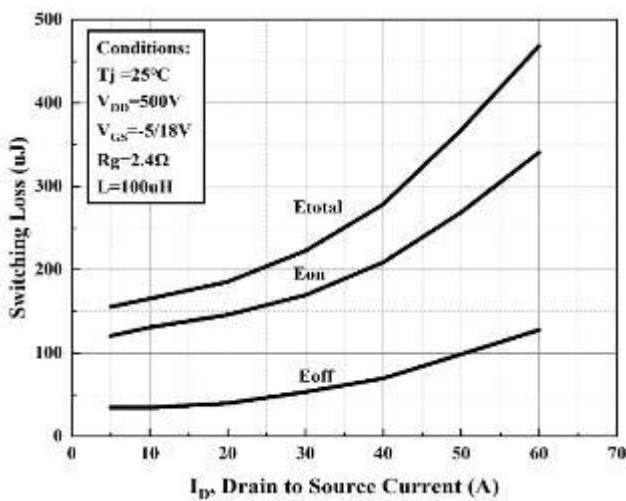


Figure 19. Clamped Inductive Switching Energy vs. Drain Current

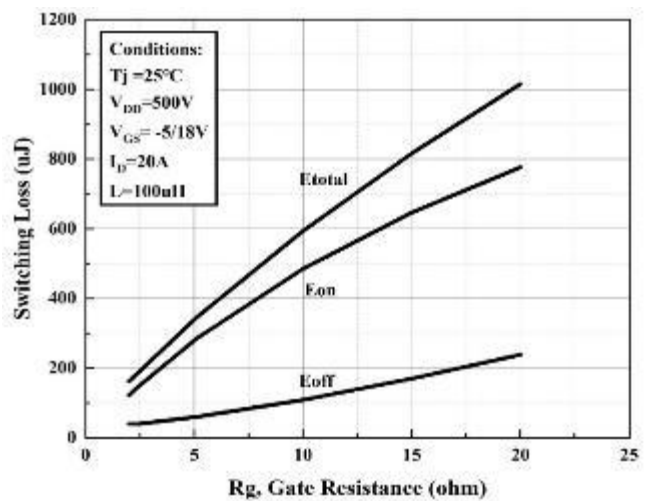


Figure 20. Clamped Inductive Switching Energy vs. Rg

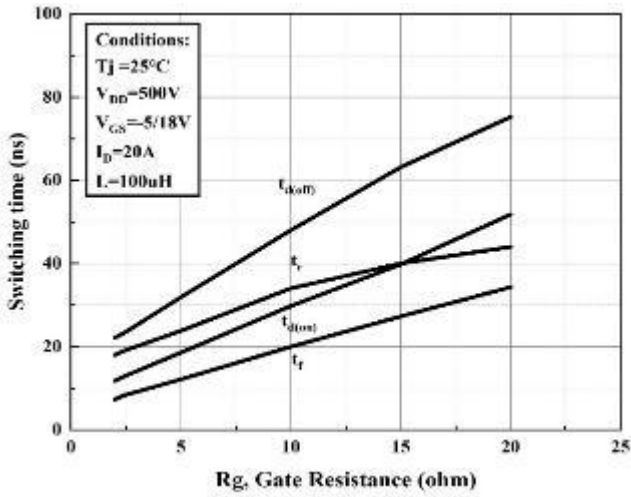


Figure 21. Switching Times vs. R_g

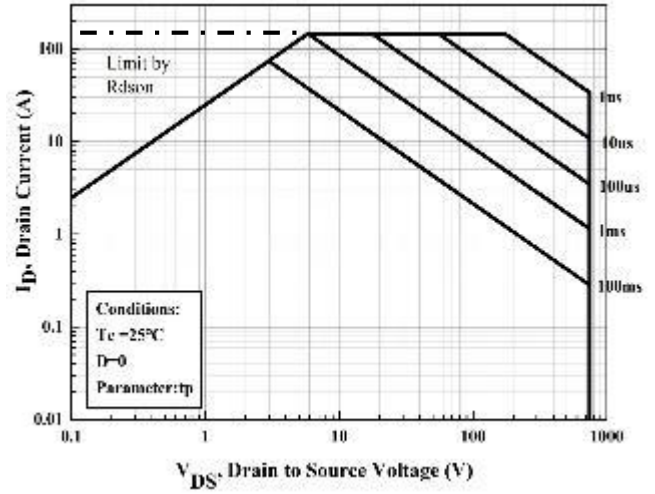


Figure 22. Safe Operating Area

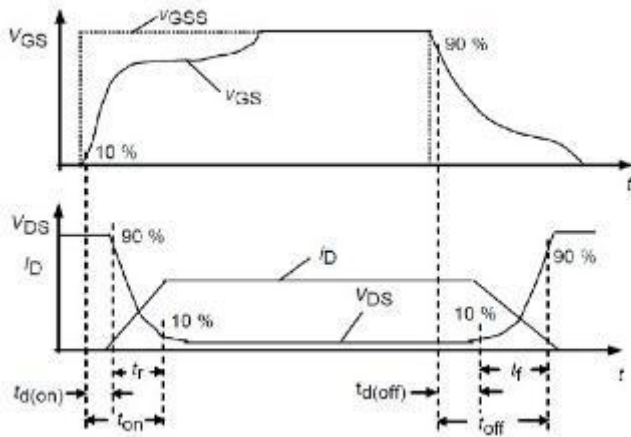


Figure 23. Switching Times Definition

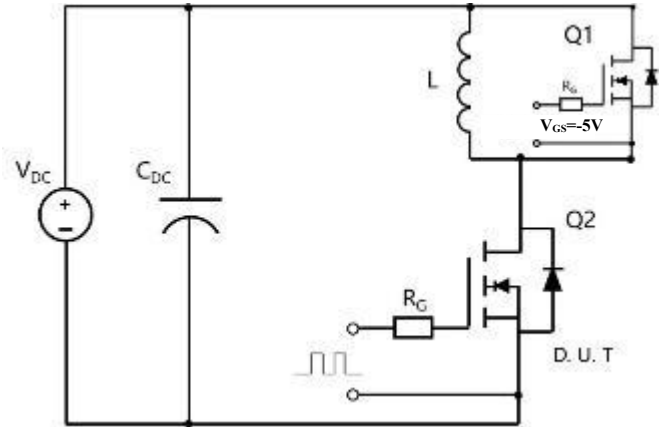
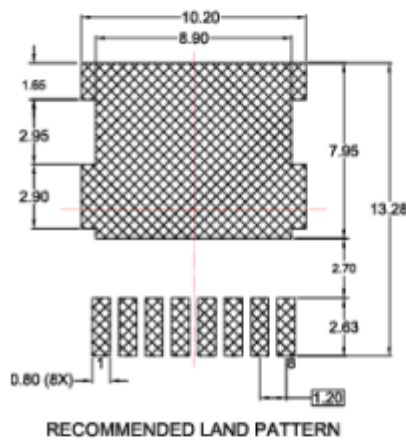
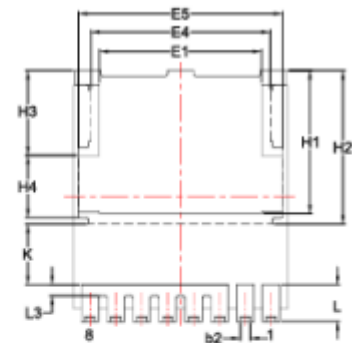
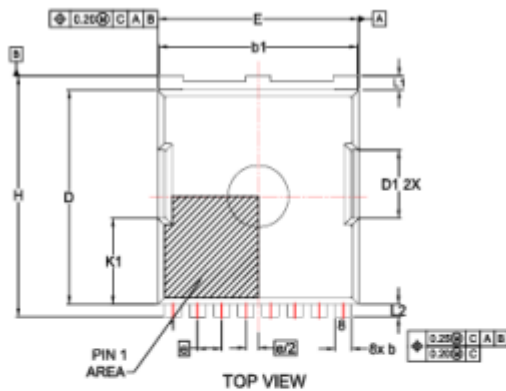


Figure 24. Clamped Inductive Switching Waveform Test Circuit



YJD207550TLYG3

■Outline Dimensions



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	2.20	2.3	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	0.70	0.80	0.90
b2	0.36	0.46	0.56
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D1	3.30		
E	9.80	9.90	10.00
E1	8.0	8.10	8.20
E4	8.40		
E5	9.40		
e	1.20 BSC		
e2	0.60 BSC		
H	11.58	11.68	11.78
H1	6.56	6.66	6.76
H2	7.05	7.15	7.25
H3	3.50		
H4	3.25		
K	2.70	2.80	2.90
K1	4.18		
L	1.63	1.73	1.83
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.30	0.40	0.50
E	8 REF		



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